

ABSTRACT OF THE DISCLOSURE

A method in which a desired pattern is compared with a finish pattern to be formed on a wafer, which is predicted from a design pattern, based on a calculation of a light beam intensity, and a deviation quantity of the finish pattern from the desired pattern at each edge of the finish pattern and the desired pattern is calculated, comprising setting a reference light beam intensity for setting the desired pattern on a wafer, setting an evaluation point for comparison of the finish pattern with the desired pattern, calculating a light beam intensity at the evaluation point, calculating a differentiation value of the light beam intensity at the evaluation point, calculating an intersection of the differentiation value with the reference light beam intensity, and calculating a difference between the intersection and the evaluation point, the difference defining an edge deviation quantity of the finish pattern from the desired pattern.